

AO8810-VB Datasheet

Dual N-Channel MOSFET

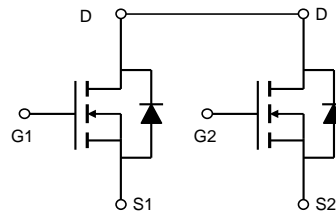
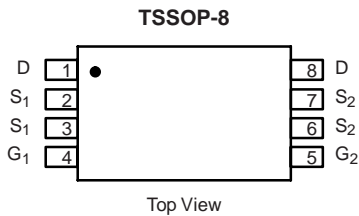
PRODUCT SUMMARY		
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)
20	0.014 at V _{GS} = 4.5 V	7.6
	0.018 at V _{GS} = 2.5 V	6.5

FEATURES

- Halogen-free Option Available
- TrenchFET[®] Power MOSFETs



Available
RoHS*
COMPLIANT



ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted					
Parameter	Symbol	10 s	Steady State	Unit	
Drain-Source Voltage	V _{DS}	20		V	
Gate-Source Voltage	V _{GS}	± 12			
Continuous Drain Current (T _J = 150 °C) ^a	I _D	T _A = 25 °C	7.6	6.2	A
		T _A = 70 °C	6.5	4.5	
Pulsed Drain Current	I _{DM}	30			
Continuous Source Current (Diode Conduction) ^a	I _S	1.5	1.0		
Maximum Power Dissipation ^a	P _D	T _A = 25 °C	1.5	1.0	W
		T _A = 70 °C	0.96	0.64	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typ.	Max.	Unit	
Maximum Junction-to-Ambient ^a	R _{thJA}	t ≤ 10 s	72	83	°C/W
		Steady State	100	120	
Maximum Junction-to-Foot (Drain)	R _{thJF}	55	70		

Notes:

a. Surface Mounted on FR4 board, t ≤ 10 s.

* Pb containing terminations are not RoHS compliant, exemptions may apply.

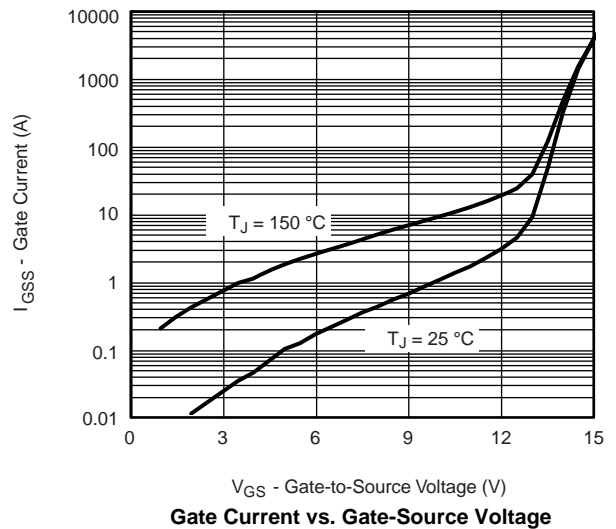
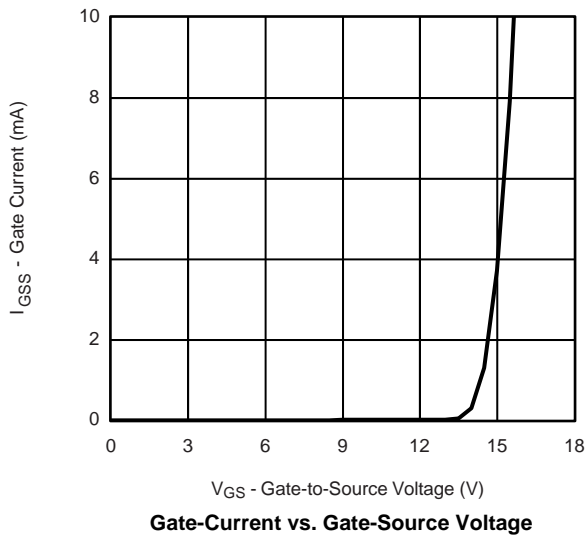
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	0.6		1.6	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\ \text{V}, V_{GS} = \pm 4.5\ \text{V}$			± 200	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 20\ \text{V}, V_{GS} = 0\ \text{V}$			1	μA
		$V_{DS} = 20\ \text{V}, V_{GS} = 0\ \text{V}, T_J = 70\text{ }^\circ\text{C}$			25	
On-State Drain Current ^b	$I_{D(on)}$	$V_{DS} \leq 5\ \text{V}, V_{GS} = 4.5\ \text{V}$	30			A
Drain-Source On-State Resistance ^b	$R_{DS(on)}$	$V_{GS} = 4.5\ \text{V}, I_D = 6.5\ \text{A}$		0.014		Ω
		$V_{GS} = 2.5\ \text{V}, I_D = 5.5\ \text{A}$		0.018		
Forward Transconductance ^b	g_{fs}	$V_{DS} = 10\ \text{V}, I_D = 6.5\ \text{A}$		30		S
Diode Forward Voltage ^b	V_{SD}	$I_S = 1.5\ \text{A}, V_{GS} = 0\ \text{V}$		0.71	1.2	V
Dynamic^a						
Total Gate Charge	Q_g	$V_{DS} = 10\ \text{V}, V_{GS} = 4.5\ \text{V}, I_D = 6.5\ \text{A}$		12	18	nC
Gate-Source Charge	Q_{gs}			2.2		
Gate-Drain Charge	Q_{gd}			3.6		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 10\ \text{V}, R_L = 10\ \Omega$ $I_D \cong 1\ \text{A}, V_{GEN} = 4.5\ \text{V}, R_G = 6\ \Omega$		245	365	ns
Rise Time	t_r			330	495	
Turn-Off Delay Time	$t_{d(off)}$			860	1300	
Fall Time	t_f			510	765	

Notes:

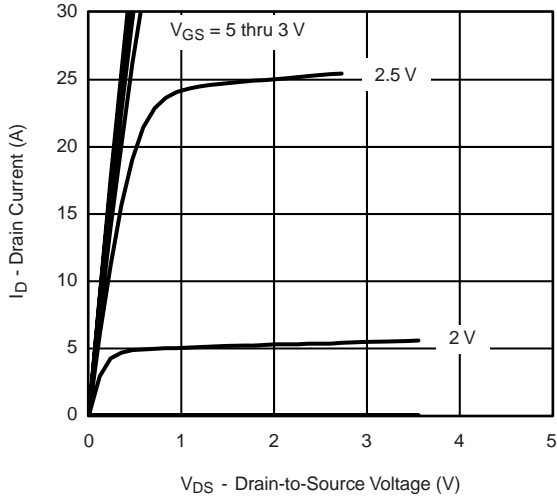
- a. For design aid only; not subject to production testing.
- b. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

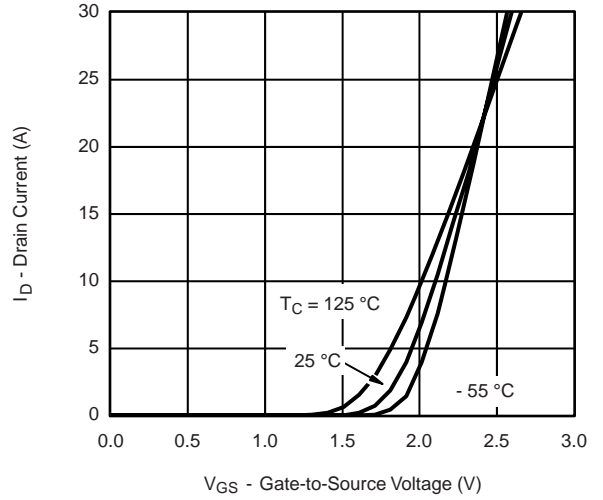
TYPICAL CHARACTERISTICS $25\text{ }^\circ\text{C}$, unless otherwise noted



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Output Characteristics



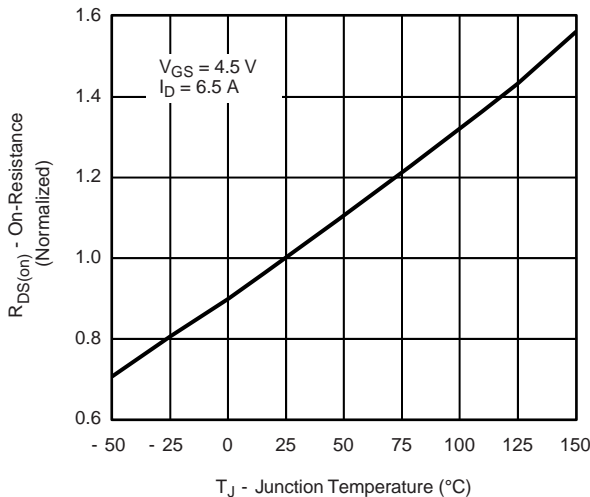
Transfer Characteristics



On-Resistance vs. Drain Current



Gate Charge



On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



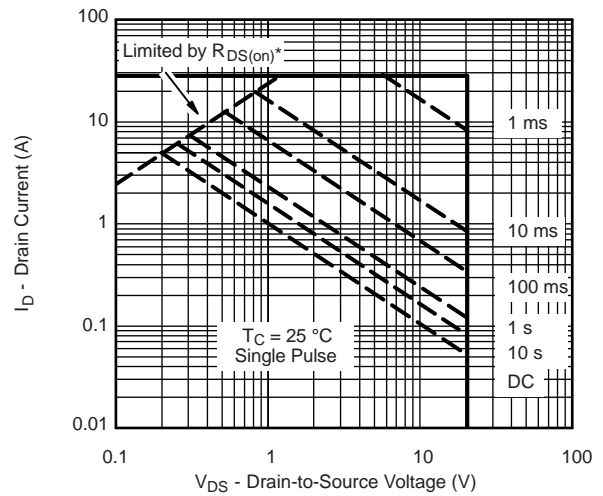
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power



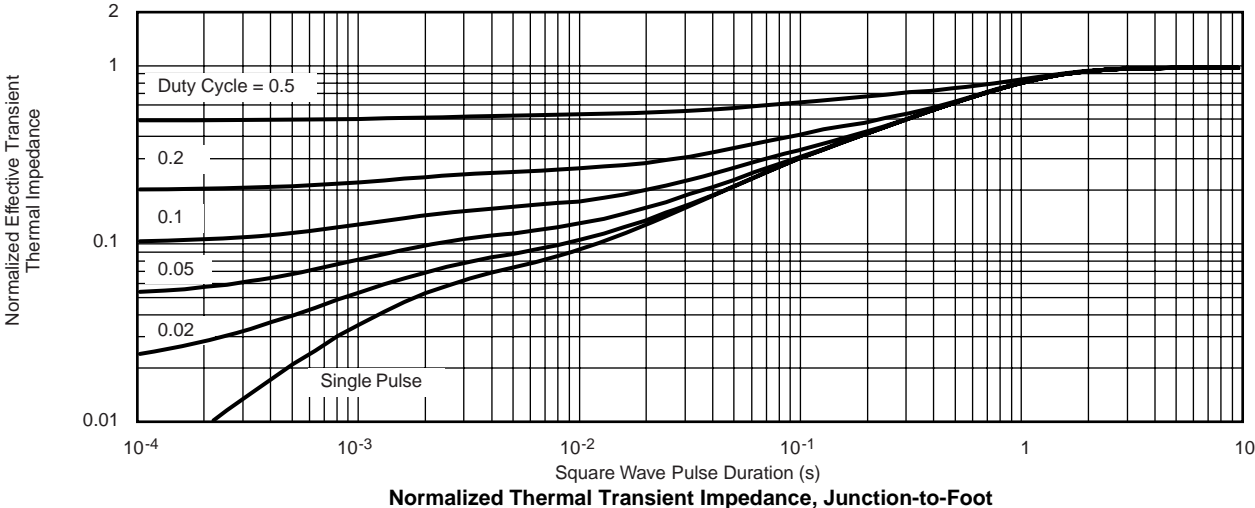
Safe Operating Area, Junction-to-Case



Normalized Thermal Transient Impedance, Junction-to-Ambient

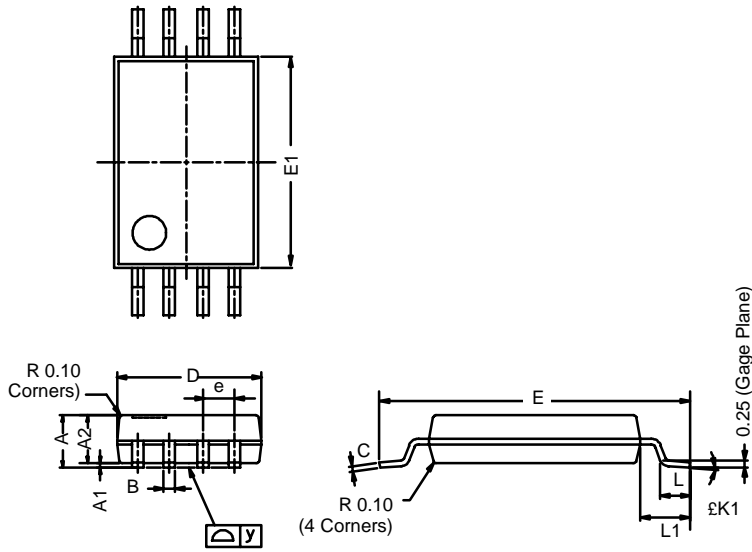
- Notes:
- Duty Cycle, $D = \frac{t_1}{t_2}$
 - Per Unit Base = $R_{thJA} = 115 \text{ } ^\circ\text{C/W}$
 - $T_{JM} - T_A = P_{DM}Z_{thJA}(t)$
 - Surface Mounted

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



TSSOP: 8-LEAD

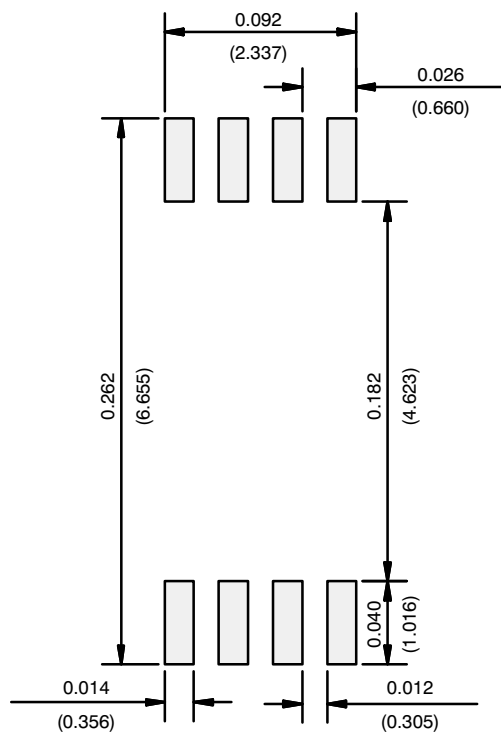
JEDEC Part Number: MO-153



Dim	MILLIMETERS		
	Min	Nom	Max
A	–	–	1.20
A ₁	0.05	0.10	0.15
A ₂	0.80	1.00	1.05
B	0.19	0.28	0.30
C	–	0.127	–
D	2.90	3.00	3.10
E	6.20	6.40	6.60
E ₁	4.30	4.40	4.50
e	–	0.65	–
L	0.45	0.60	0.75
L ₁	0.90	1.00	1.10
Y	–	–	0.10
$\epsilon K1$	0°	3°	6°

ECN: S-03946—Rev. G, 09-Jul-01
DWG: 5844

RECOMMENDED MINIMUM PADS FOR TSSOP-8



Recommended Minimum Pads
Dimensions in Inches/(mm)

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